

NOTES:

1. All dimensions are in millimeter;
2. Tolerance is $\pm 0.25\text{mm}$, unless other specified;
3. Pin length, housing color, marking no & circuit diagram can be customized;
4. Specifications are subject to change without notice.

Chip Material: AlGaInP / GaAs Ultra Bright Red LED Chip

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PARAMETER	SYMBOL	MAXIMUM RATING	UNIT
Power Dissipation	PD	72	mW
Peak Forward Current (1/10 Duty Cycle, 0.1 Ms Pulse Width)	IPEAK	90	mA
DC Forward Current	IF	30	mA
Reverse Voltage	VR	5	V
Operating Temperature Range	TA	-40°C to +85°C	
Storage Temperature Range	TSTG	-40°C to +85°C	
Solder temperature 1/16 inch below seating plane for 3 seconds at 260°C			

ELECTRICAL OPTICAL CHARACTER AND CURVES (Ta = 25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	LOCATION	TEST CONDITION
Forward Voltage	V _F	-	2.05	2.40	V	Per Chip	I _F = 20mA
Luminous Intensity	I _v	34	38	60	mcd	Per Chip	I _F = 20mA
Peak Emission Wavelength	λ _p	-	645	-	nm	Per Chip	I _F = 20mA
Dominant Emission Wavelength	λ _d	630	635	638	nm	Per Chip	I _F = 20mA
Spectral Line Half-Width	Δλ _{1/2}	-	20	-	nm	Per Chip	I _F = 20mA
Reverse Current	I _R	-	-	10	uA	Per Chip	V _R = 5V

Note:

1. Luminous intensity tolerance is ±10%;
2. Dominant Emission Wavelength tolerance is ±5%.

FIG. 1 Forward Current Vs. Forward Voltage

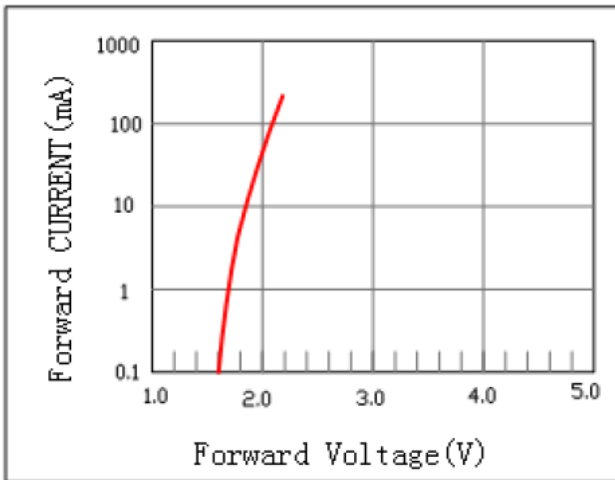


FIG. 2 Relative Intensity Vs. Forward Current

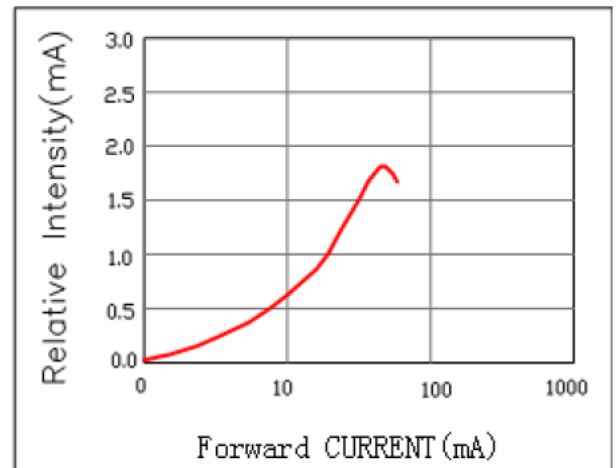


FIG. 3 Forward Voltage Vs. Temperature

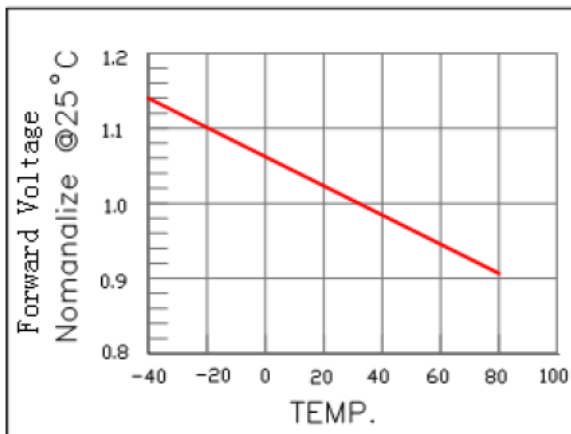


FIG. 4 Relative Intensity Vs. Temperature

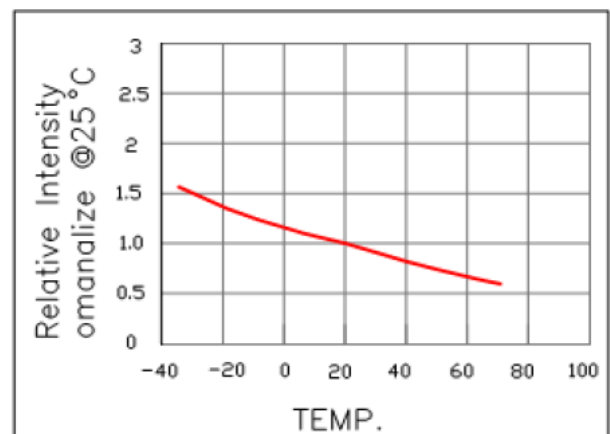


FIG. 5 Relative Intensity Vs. Wavelength

